STD100N03L-1
STD100N03L

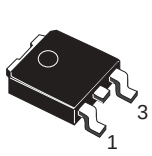
N-CHANNEL 30V - 0.0045Ω - 80A - DPAK - IPAK
Planar STripFET™ MOSFET

General features

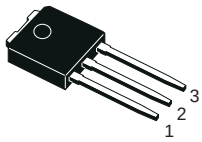
Type	V_{DSSS}	$R_{DS(on)}$	I_D	Pw
STD100N03L	30 V	<0.0055 Ω	80 A(1)	110 W
STD100N03L-1	30 V	<0.0055 Ω	80 A(1)	110 W

- 100%AVALANCHE TESTED
- SURFACE-MOUNTING DPAK (TO-252)
- LOGIC LEVEL THRESHOLD

Package

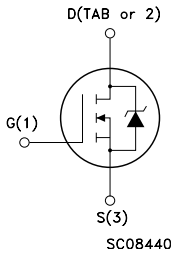


DPAK



IPAK

Internal schematic diagram



Description

This MOSFET is the latest refinement of STMicroelectronic unique “Single Feature Size™” stripbased process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics, low gate charge and less critical aligment steps therefore a remarkable manufacturing reproducibility. This new improved device has been specifically designed for Automotive application and DC-DC converters.

Applications

- HIGH CURRENT, HIGH SWITCHING DC-DC CONVERTER
- AUTOMOTIVE

Order codes

Sales Type	Marking	Package	Packaging
STD100N03LT4	D100N03L	DPAK	TAPE & REEL
STD100N03L-1	D100N03L-1	IPAK	TUBE

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage (V_{GS} = 0)	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D *Note* 1	Drain Current (continuous) at T_C = 25°C	80	A
I_D	Drain Current (continuous) at T_C = 100°C	70	A
I_{DM} *Note* 2	Drain Current (pulsed)	320	A
P_{TOT}	Total Dissipation at T_C = 25°C	110	W
	Derating Factor	0.73	W/°C
dv/dt *Note* 3	Peak Diode Recovery Voltage Slope	3.9	V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 175	°C

Table 2. Thermal Data

Rthj-case	Thermal Resistance Junction-case Max	1.36	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	100	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose (for 10sec. 1.6 mm from case)	275	°C

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AV}	Not-Repetitive Avalanche Current (pulse width limited by Tj max)	40	A
E_{AS}	Single pulsed avalanche Energy (starting Tj=25°C, I_D=I_{AV}, V_{DD} = 24V	500	mJ

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/Off states

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250µA, V_{GS}= 0	30			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating, V_{DS} = Max Rating, T_c=125°C			10 100	µA µA
I_{GSS}	Gate Body Leakage Current (V_{DS} = 0)	V_{DS} = ± 20 V			±200	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D = 250 µA	1			V
$R_{DS(on)}$	Static Drain-Source On Resistance	V_{GS}= 10 V, I_D= 40 A V_{GS}= 5 V, I_D= 20 A		0.0045 0.008	0.0055 0.01	Ω Ω
$R_{DS(on)}$	Static Drain-Source On Resistance	V_{GS}= 10 V, I_D= 40 A @125°C V_{GS}= 5 V, I_D= 20 A @125°C		0.0068 0.0146		Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} *Note* 4	Forward Transconductance	V_{DS} = 10 V, I_D= 15 A		31		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} =0		2060 728 67		pF pF pF
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 24 V, I_D = 80 A, V_{GS} = 5V (see Figure 15)		20 7 7.5	27	nC nC nC
R_G	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.9		Ω

Table 6. Switching time

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 15 V, I_D = 40 A R_G= 4.7 Ω, V_{GS}= 10V, (see Figure 14)		9 205		ns ns
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 15 V, I_D = 40 A R_G= 4.7 Ω, V_{GS}= 10V, (see Figure 14)		31 35		ns ns

Table 7. Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} *Note* 2	Source-Drain Current Source-Drain Current (pulsed)				80 320	A A
V_{SD} *Note* 4	Forward On Voltage	I_{SD} = 40 A, V_{GS} = 0			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 80 A, di/dt = 100 A/µs V_{DD} = 25 V, T_j = 150 °C (see Figure 16)		40 40 2		ns nC A

(1) Current limited by package.

(2) Pulse width limited by safe operating area

(3) $I_{SD} \leq 80A$, $di/dt \leq 360$ A/µs, $V_{DS} \leq V_{(BR)DSS}$, $Tj \leq Tj_{MAX}$

(4) Pulsed: Pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe Operating Area

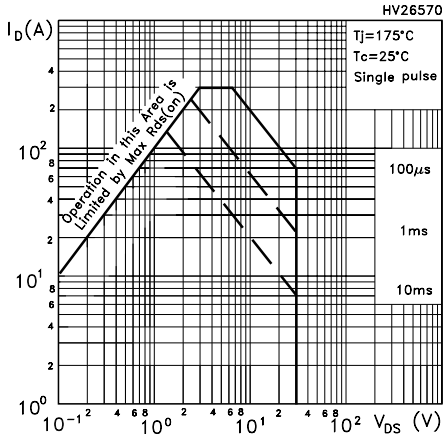


Figure 2. Thermal Impedance

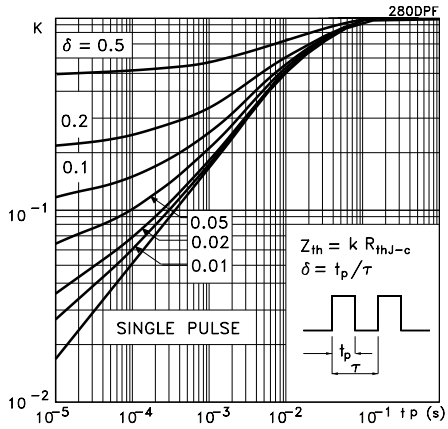


Figure 3. Output Characteristics

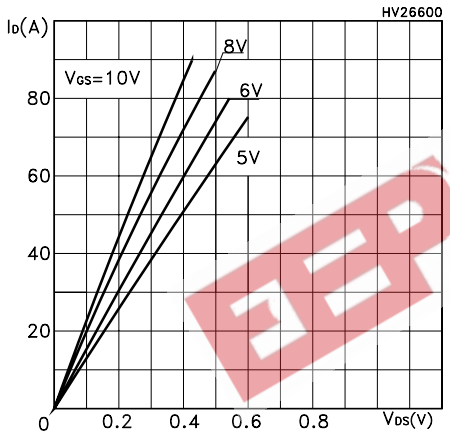


Figure 4. Transfer Characteristics

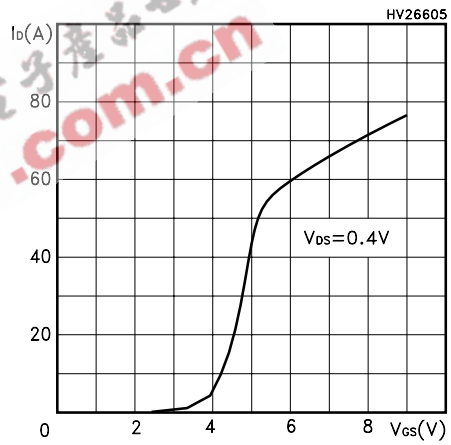


Figure 5. Transconductance

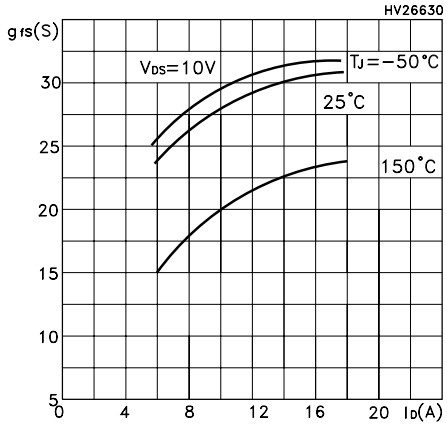


Figure 6. Static Drain-source on Resistance

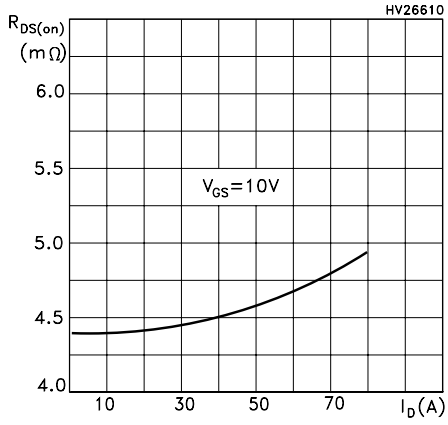


Figure 7. Gate Charge vs Gate-source Voltage

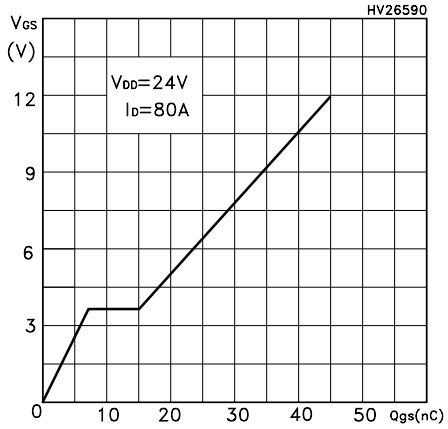


Figure 8. Capacitance Variation

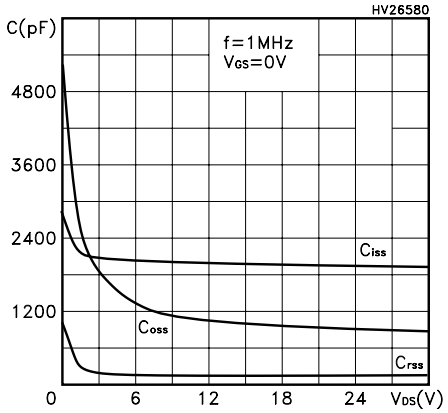


Figure 9. Normalized Gate Thereshold Voltage vs Temperature

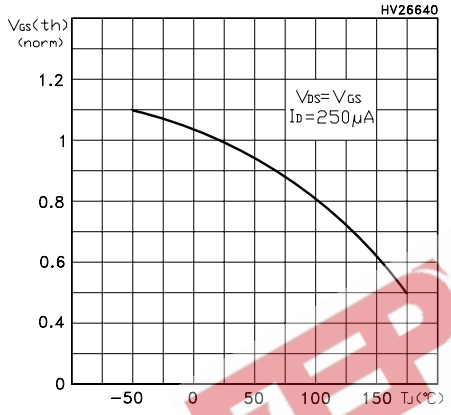


Figure 10. Normalized BVDSS vs Temperature

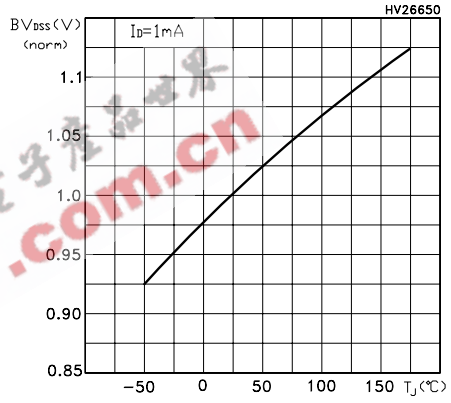


Figure 11. Normalized on Resistance vs Temperature

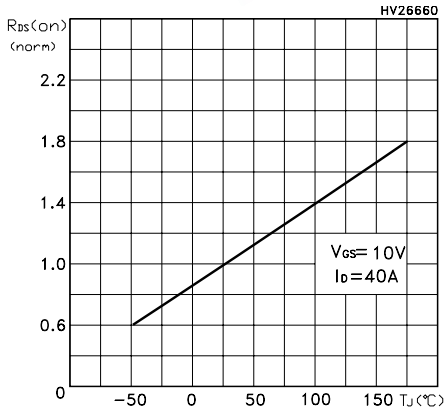


Figure 12. Source-Drain Diode Forward Characteristics

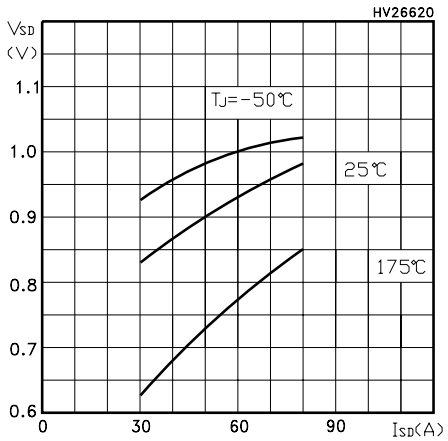
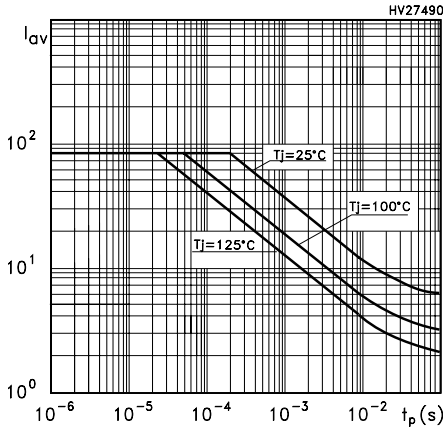


Figure 13. Allowable Iav vs. Time in Avalanche



The previous curve gives the single pulse safe operating area for unclamped inductive loads, under the following conditions:

$P_{D(AVE)} = 0.5*(1.3*BV_{DSS} * I_{AV})$

$E_{AS(AR)} = P_{D(AVE)} * t_{AV}$

Where:

I_{AV} is the Allowable Current in Avalanche

$P_{D(AVE)}$ is the Average Power Dissipation in Avalanche (Single Pulse)

t_{AV} is the Time in Avalanche

3 Test Circuits

Figure 14. Switching Times Test Circuit For Resistive Load

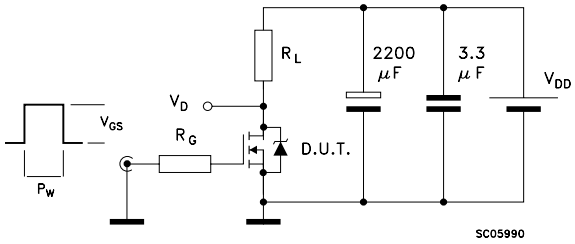


Figure 15. Gate Charge Test Circuit

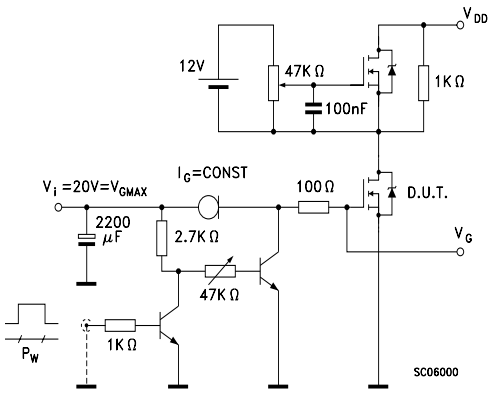
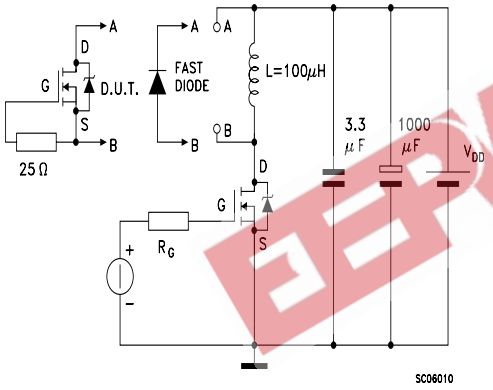


Figure 16. Test Circuit For Indictive Load Switching and Diode Recovery Times

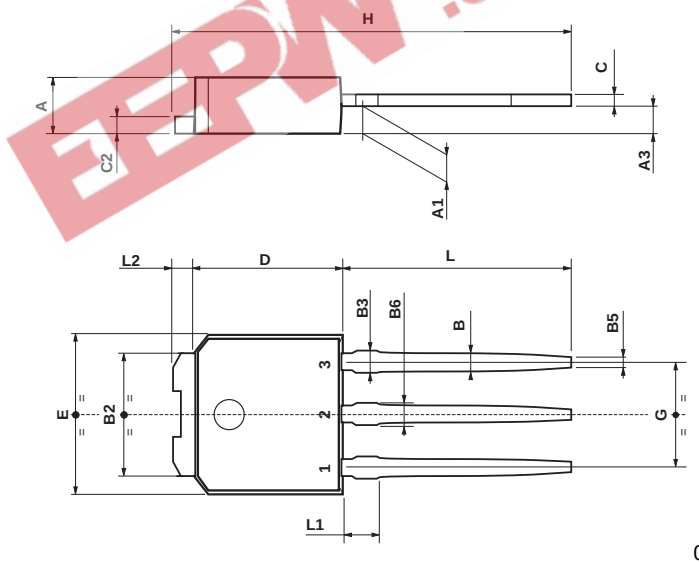


4 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-251 (IPAK) MECHANICAL DATA

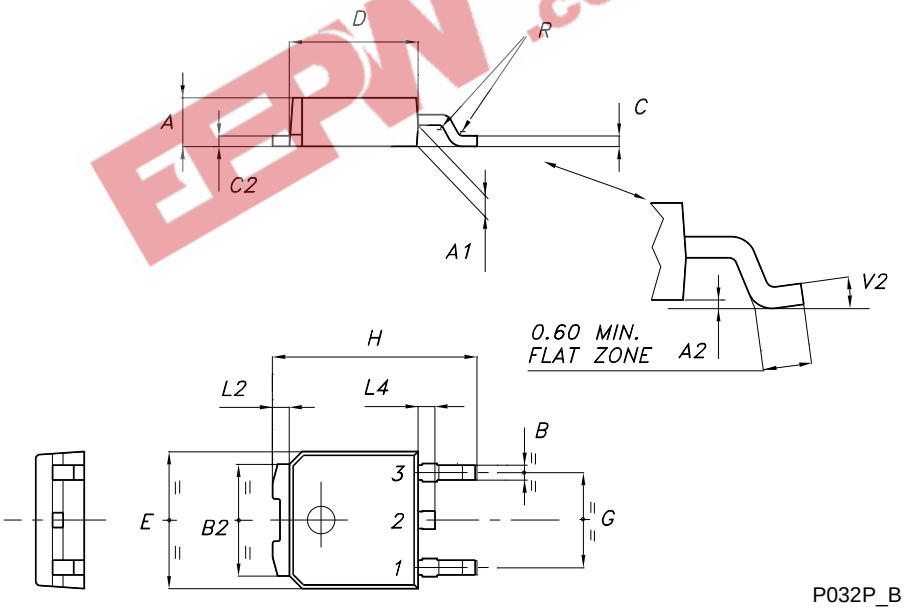
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



0068771-E

TO-252 (DPAK) MECHANICAL DATA

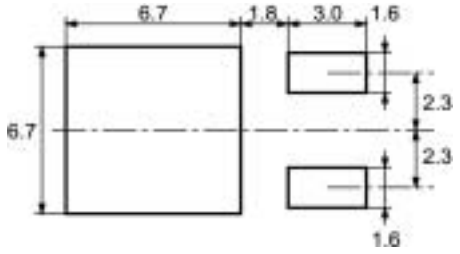
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



P032P_B

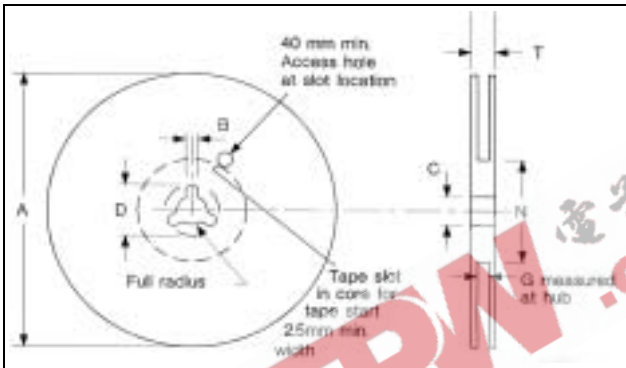
5 Packing mechanical data

DPAK FOOTPRINT



All dimensions are in millimeters

TAPE AND REEL SHIPMENT



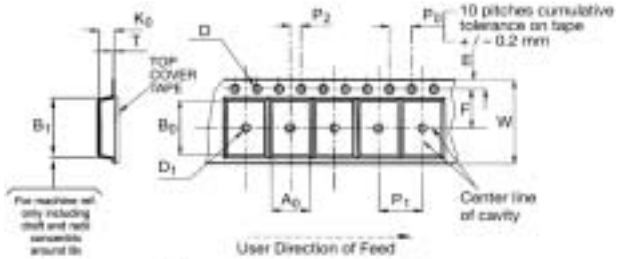
REEL MECHANICAL DATA

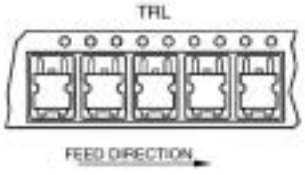
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

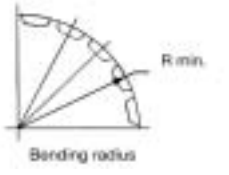
BASE QTY	BULK QTY
2500	2500

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641







6 Revision History

Date	Revision	Changes
01-Sep-2005	1	Initial release.
14-Sep-2005	2	Value changed on *Figure 1*